

NVATS4A102PZ

Power MOSFET

-30 V, 18.5 mΩ, -44 A, P-Channel



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The NVATS4A102PZ is a power MOSFET designed for compact size and high efficiency which can achieve high thermal performance. AEC-Q101 qualified MOSFET and PPAP capable suitable for automotive applications.

Features

- Low On-Resistance
- High Current Capability
- 100% Avalanche Tested
- AEC-Q101 qualified and PPAP capable
- ATPAK package is pin-compatible with DPAK (TO-252)
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- Reverse Battery Protection
- Load Switch
- Automotive Front Lighting
- Automotive Body Controllers

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	-30	V
Gate to Source Voltage	V _{GSS}	±20	V
Drain Current (DC)	I _D	-44	A
Drain Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I _{DP}	-132	A
Power Dissipation Tc = 25°C	P _D	48	W
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C
Avalanche Energy (Single Pulse) (Note 2)	E _{AS}	58	mJ
Avalanche Current (Note 3)	I _{AV}	-20	A

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2 : V_{DD} = -10 V, L = 200 μH, I_{AV} = -20 A

3 : L ≤ 200 μH, Single pulse

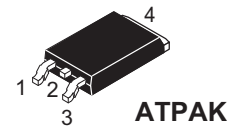
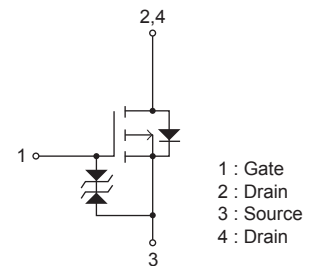
THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Case Steady State (Tc = 25°C)	R _{θJC}	3.1	°C/W
Junction to Ambient (Note 4)	R _{θJA}	80.4	°C/W

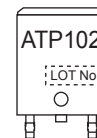
Note 4 : Surface mounted on FR4 board using a 130 mm², 1 oz. Cu pad.

V _{DSS}	R _{DS(on)} Max	I _D Max
-30 V	18.5 mΩ @ -10 V	-44 A
	31 mΩ @ -4.5 V	

ELECTRICAL CONNECTION P-Channel



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

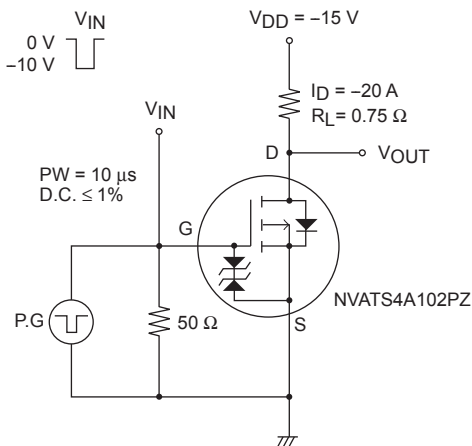
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ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 5)

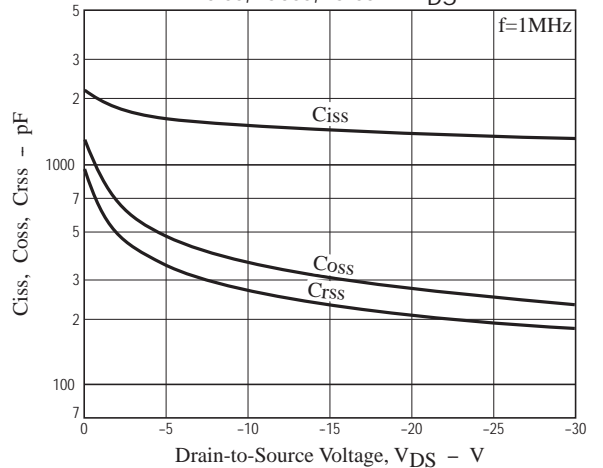
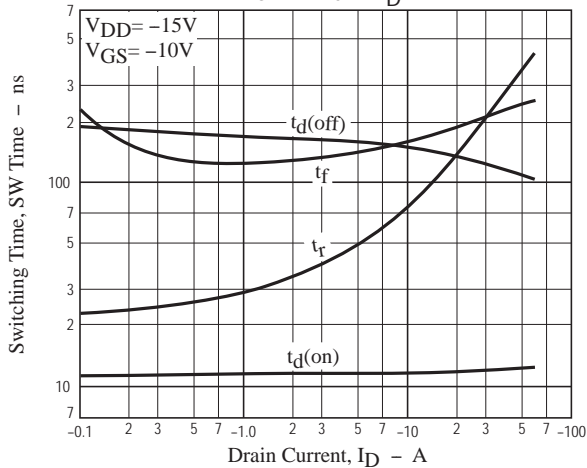
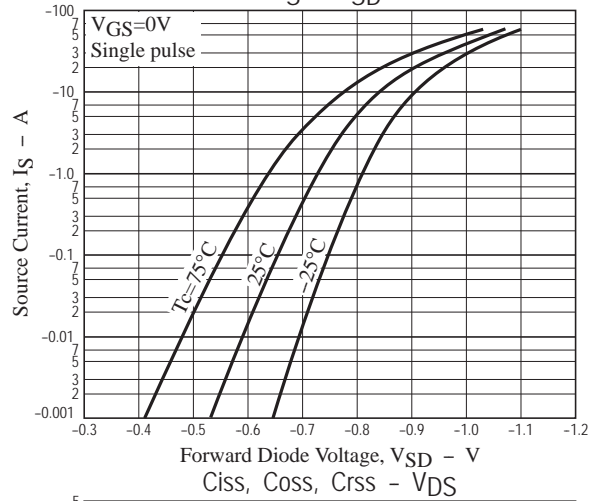
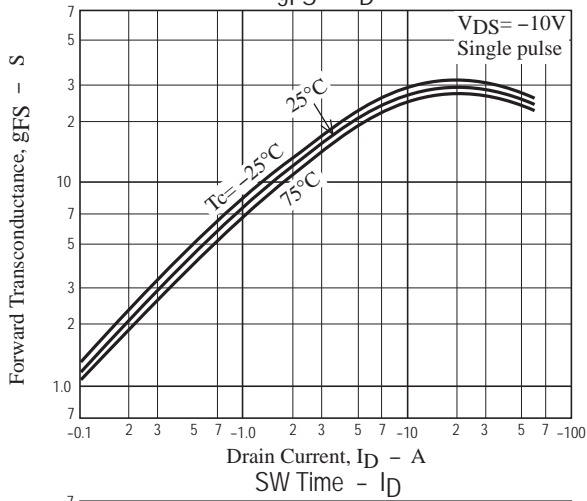
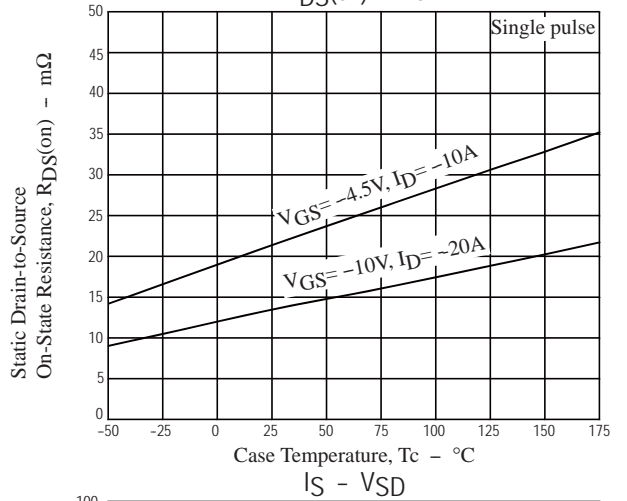
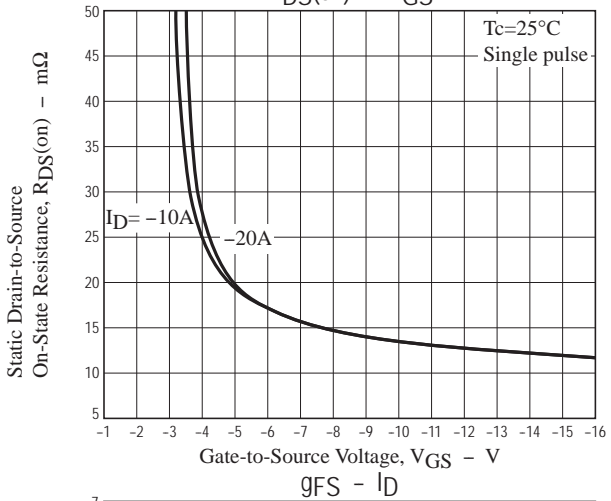
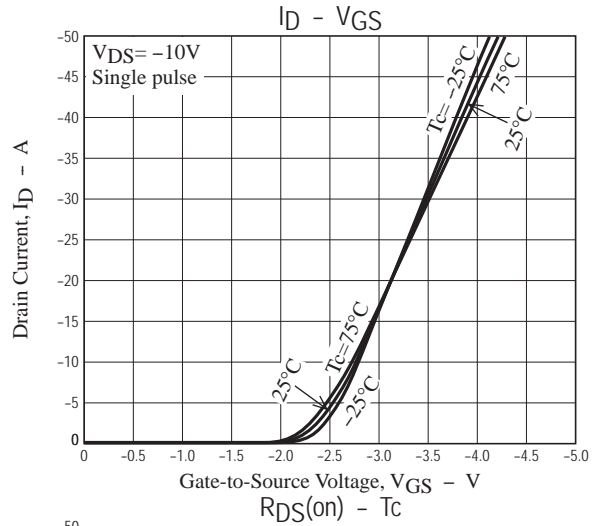
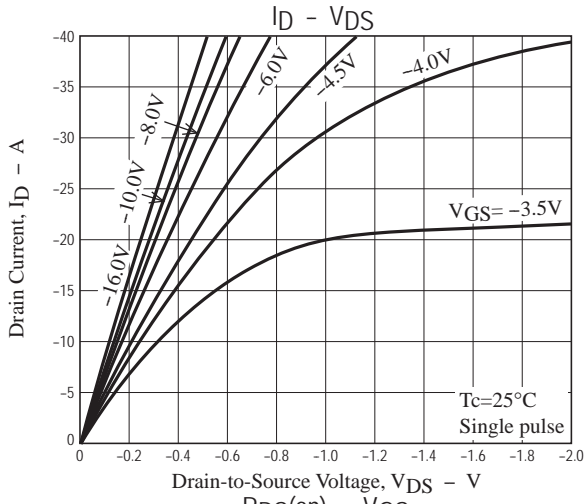
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V(BR)DSS	I _D = -1 mA, V _{GS} = 0 V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V			-1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = -10 V, I _D = -1 mA	-1.2		-2.6	V
Forward Transconductance	g _{FS}	V _{DS} = -10 V, I _D = -20 A		29		S
Static Drain to Source On-State Resistance	R _{DS(on)1}	I _D = -20 A, V _{GS} = -10 V		14	18.5	mΩ
	R _{DS(on)2}	I _D = -10 A, V _{GS} = -4.5 V		22	31	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V, f = 1 MHz		1,490		pF
Output Capacitance	C _{oss}			360		pF
Reverse Transfer Capacitance	C _{rss}			270		pF
Turn-ON Delay Time	t _{d(on)}		See Fig.1		11	
Rise Time	t _r			135		ns
Turn-OFF Delay Time	t _{d(off)}			135		ns
Fall Time	t _f			185		ns
Total Gate Charge	Q _g	V _{DS} = -15 V, V _{GS} = -10 V, I _D = -40 A		34		nC
Gate to Source Charge	Q _{gs}			4.2		nC
Gate to Drain "Miller" Charge	Q _{gd}			11.5		nC
Forward Diode Voltage	V _{SD}		I _S = -40 A, V _{GS} = 0 V		-0.99	-1.5

Note 5 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

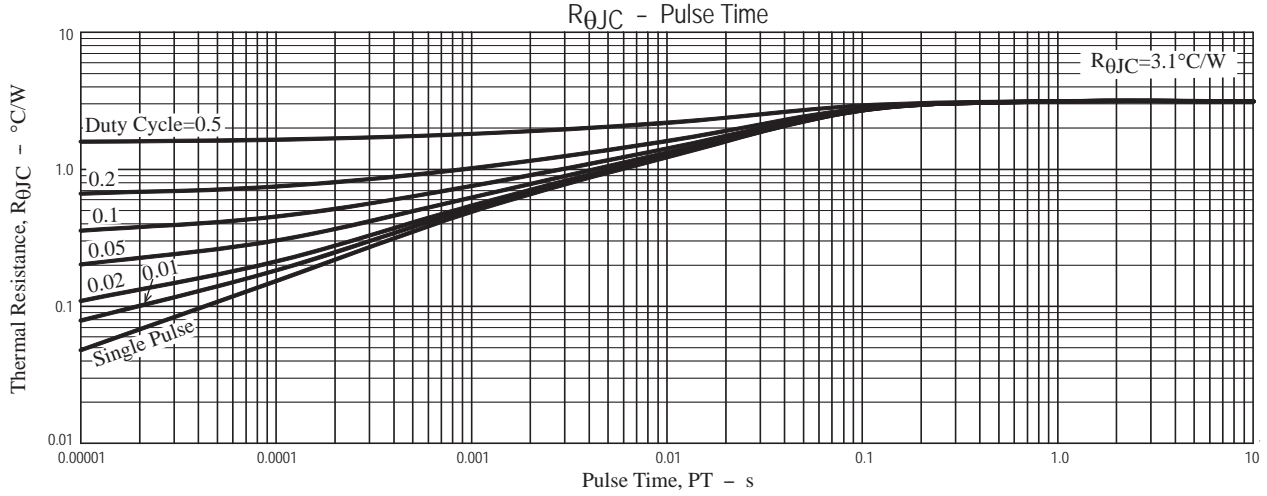
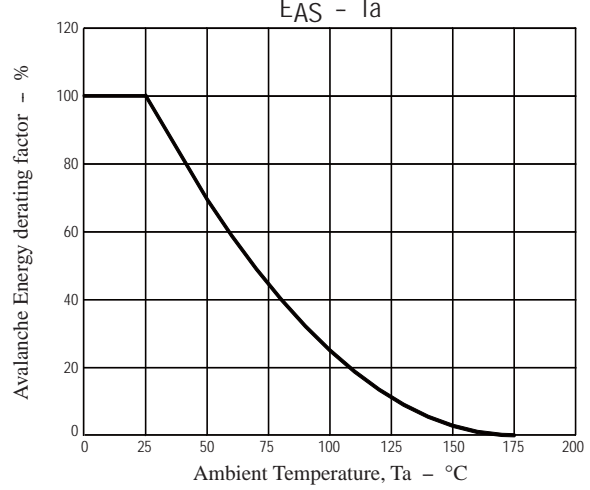
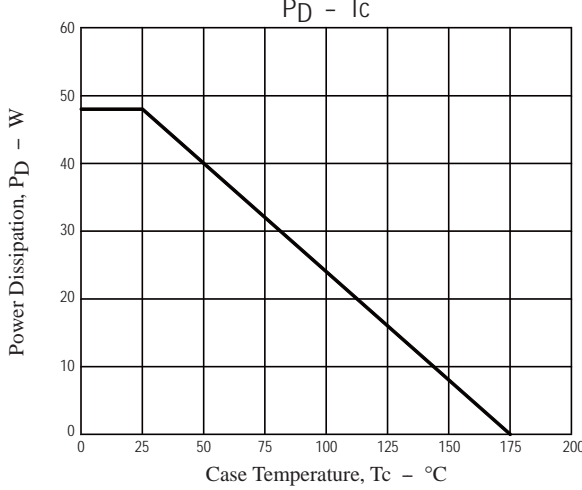
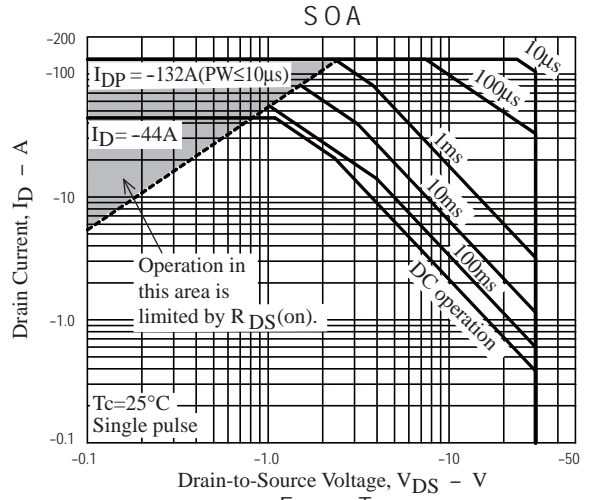
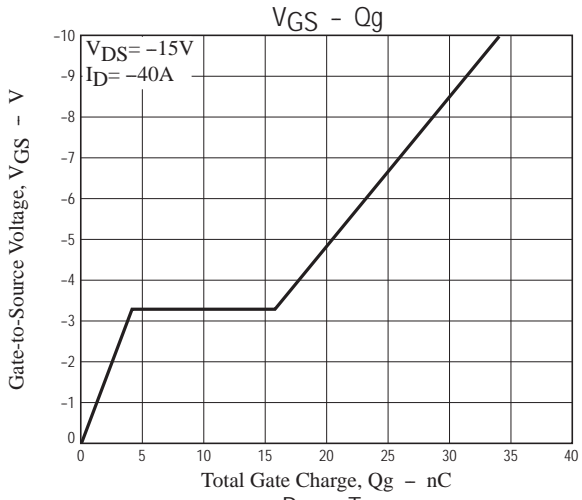
Fig.1 Switching Time Test Circuit



NVATS4A102PZ



NVATS4A102PZ



NVATS4A102PZ

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
NVATS4A102PZT4G	ATP102	DPAK(Single Gauge) / ATPAK (Pb-Free / Halogen Free)	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the NVATS4A102PZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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